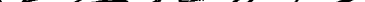


<b>Form PTO-1449</b> (Rev. 2-32)		<b>U.S. Department of Commerce</b> <b>Patent &amp; Trademark Office</b>		Atty. Docket No.  Q76117	Serial No.: <u>10/600,833</u> Confirmation No.: <u>To be Assigned</u>	
<b>INFORMATION DISCLOSURE STATEMENT</b> (Use several sheets if necessary)				Applicant: <u>Hiroyuki KIYOKU, et al.</u>		
<u>INS F:1-A 6/23/03</u>				Filing Date: <u>06/23/03</u>	Prior Art Group: <del>2822</del> <u>2826</u>	
<b>U.S. PATENT DOCUMENTS</b>						
Examiner Initial	Document Number	Date	Name	Class	Sub-Class	Filing Date (if appropriate)
<u>TD</u>	4,482,422	11/13/1984	McGinn et al.	117	95	
<u>TD</u>	4,578,142	03/25/1986	Corboy et al.	117	89	
<u>TD</u>	4,908,074	03/13/1990	Hosoi et al.	148	33.2	
<u>TD</u>	5,239,188	08/24/1993	Takeuchi et al.	257	76	
<u>TD</u>	5,247,533	09/21/1993	Okazaki et al.	372	45	
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<u>TD</u>	5,364,815	11/15/1994	Osada	438	489	
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	Document	Date	Country	Class	Sub-class	Translation Yes/No
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<u>TD</u>	7-201745 A	08/04/1995	JAPAN	H01L	021/205	
<u>TD</u>	WO 97/11518	03/27/1997	PCT	H01S	3/18	Yes-EP 0 852 416 A1
<u>TD</u>	0 852 416 A1	07/08/1998	EP	H01S	3/18	
<u>TD</u>	WO 99/44224	09/02/1999	PCT	H01L	21/20	
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>						
	International Search Report, PCT/US98/01640, July 14, 1998					
<u>TD</u>	Defendant Nichia America Corporation's Motion for Partial Summary Judgment, <i>North Carolina State University and Cree, Inc., v. Nichia Corporation and Nichia America Corporation</i> , No: 5:00-CV-703-F(2), U.S. District Court for the Eastern District of North Carolina Southern Division, Dec. 11, 2000					
<u>TD</u>	International Search Report, PCT/US99/04346, June 9, 1999					
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<u>TD</u>	Nakamura, Shuji and Gerhard Fasol, <i>The Blue Laser Diode: GaN Based Light Emitters and Lasers</i> , Berlin: Springer, 1997, pp. 282-304					
EXAMINER: <u>[Signature]</u>			DATE CONSIDERED: <u>4/5/05</u>			
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<b>INFORMATION DISCLOSURE STATEMENT</b> (Use several sheets if necessary)				Applicant: Hiroyuki KIYOKU, et al.			
IDS Filed 6/23/03				Filing Date: 06/23/03		Prior Art Group: 2822-2826	
<b>U.S. PATENT DOCUMENTS</b>							
Examiner Initial	Document Number	Date	Name	Class	Sub-Class	Filing Date (if appropriate)	
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EXAMINER:			DATE CONSIDERED: 4/6/05				
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)					
Examiner Initial		Document			
TB		International Search Report, PCT/US99/12967, October 18, 1999			
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